Product Summary

$V_{(BR)DSS}$	$R_{DS(on)\ max}$	I_D T_A = +25°C
-30V	80mΩ@ V_{GS} = -10V	-4.0A
	140mΩ@ V_{GS} =-4.5V	—

Description

This new generation Trench MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance.

Applications

- Power management functions
- Portable Equipment
- Battery Charging

Features and Benefits

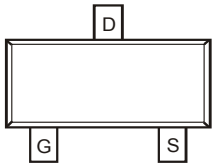
- Low On-Resistance
- Fast Switching Speed
- 4.5V Gate Drive Capability
- Thermally Enhanced SOT23 package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

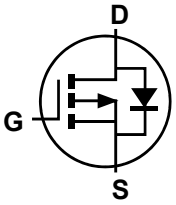
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

SOT23

Top View



Pin Configuration



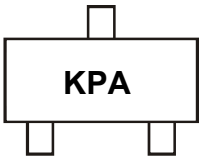
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
ZXMP3F30FHTA	Standard	SOT23	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



KPA = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

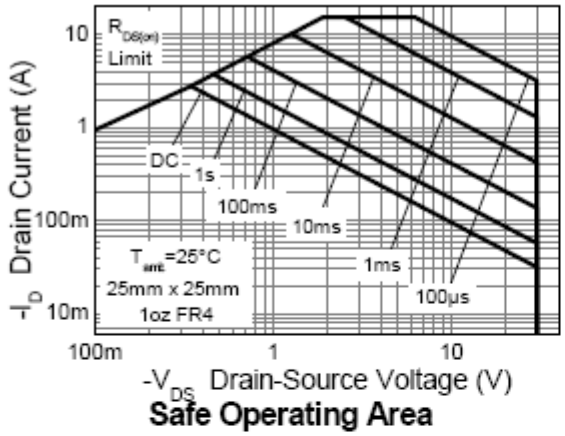
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

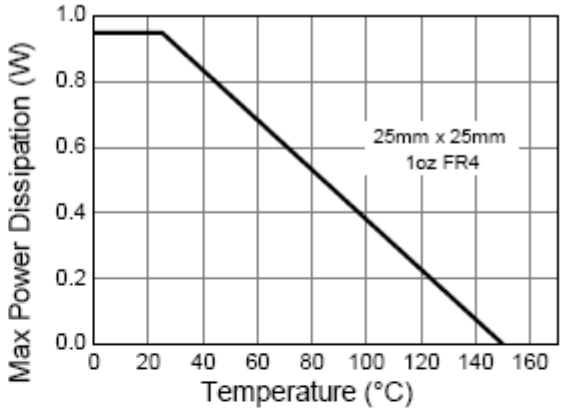
Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current, V_{GS} = -10V	T_A = +25°C (Note 6)	I_D	-3.4	A
	T_A = +70°C (Note 6)		-2.7	
	T_A = +25°C (Note 5)		-2.8	
	T_L = +25°C (Note 8)		-4.0	
Pulsed Drain Current (Note 7)		I_{DM}	-15.3	A
Continuous Source Current (Body Diode) (Note 6)		I_S	-2	A
Pulsed Source Current (Body Diode) (Note 7)		I_{SM}	-15.3	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

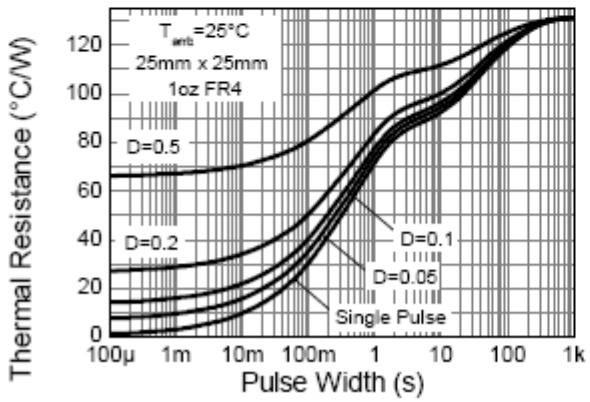
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5) Linear Derating Factor	T_A = +25°C (Note 5)	P_D	0.95	W
			7.6	mW/°C
	T_A = +25°C (Note 6)		1.4	W
			11.2	mW/°C
	T_L = +25°C (Note 8)		1.96	W
			15.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	131	°C/W
	(Note 6)		89	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C



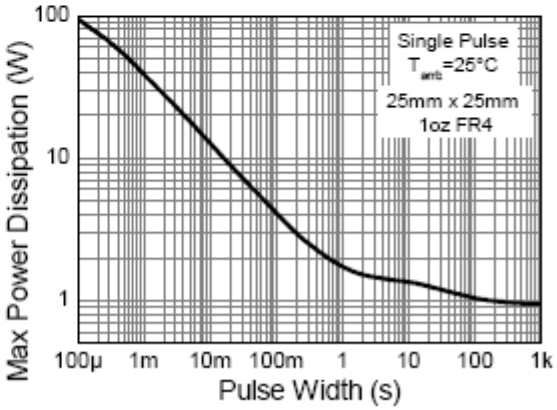
Safe Operating Area



Derating Curve



Transient Thermal Impedance



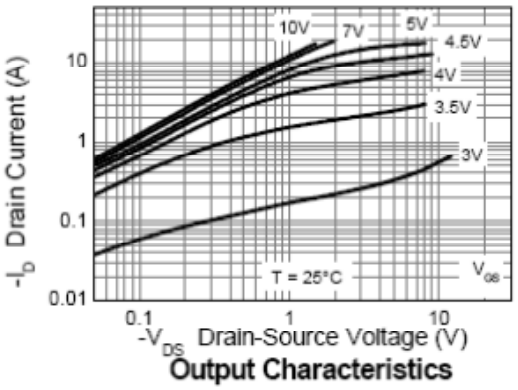
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

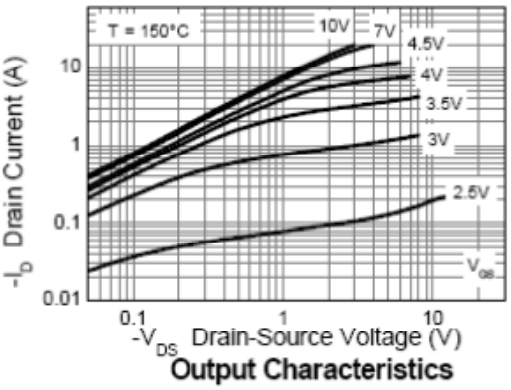
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	nA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	-1	—	-3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance (Note 9)	$R_{DS\ (ON)}$	—	—	80 140	mΩ	V_{GS} = -10V, I_D = -2.5A V_{GS} = -4.5V, I_D = -1.9A
Forward Transconductance (Note 9 & 10)	g_{fs}	—	5	—	S	V_{DS} = -15V, I_D = -3A
Diode Forward Voltage (Note 9)	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -1.7A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	370	—	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	72	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	38	—	pF	
GATE CHARACTERISTICS						
Total Gate Charge	Qg	—	7	—	nC	V_{DS} = -15V, V_{GS} = -10V, I_D = -3A
Gate-Source Charge	Q_{gs}	—	1.2	—		
Gate-Drain Charge	Q_{gd}	—	1.3	—		
SWITCHING CHARACTERISTICS (Note 10 & 11)						
Turn-On Delay Time	$t_{d(on)}$	—	1.3	—	ns	V_{DS} = -15V, V_{GS} = -10V, I_D = -1A, R_G = 6.0Ω
Rise Time	t_r	—	2.6	—		
Turn-On Delay Time	$t_{d(off)}$	—	49	—		
Rise Time	t_f	—	22	—		
SOURCE-DRAIN DIODE CHARACTERISTICS (Note 11)						
Reverse Recovery Time	t_{rr}	—	14.6	—	ns	IS= -1.5A,di/dt=100A/µs
Reverse Recovery Charge	Q_{rr}	—	9.5	—	nC	

Notes:
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. Mounted on FR4 PCB measured at t ≤10 sec.
7. Repetitive rating on 25mm x 25mm FR4 PCB, D=0.02, pulse width 300µs – pulse width limited by maximum junction temperature.
8. Thermal resistance from junction to solder-point (at the end of the drain lead).
9. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
10. Switching characteristics are independent of operating junction temperature.
11. For design aid only, not subject to production testing.

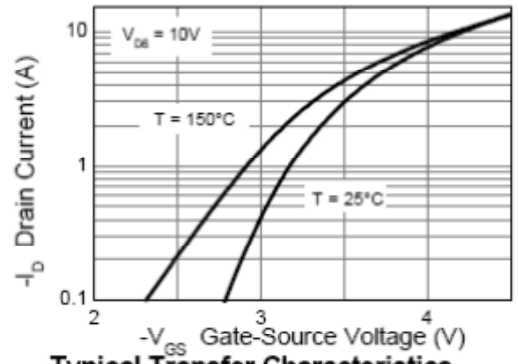
Typical Characteristics



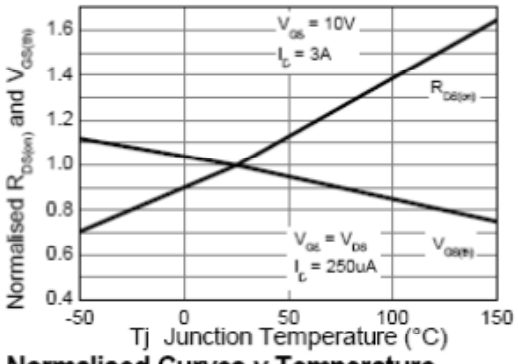
Output Characteristics



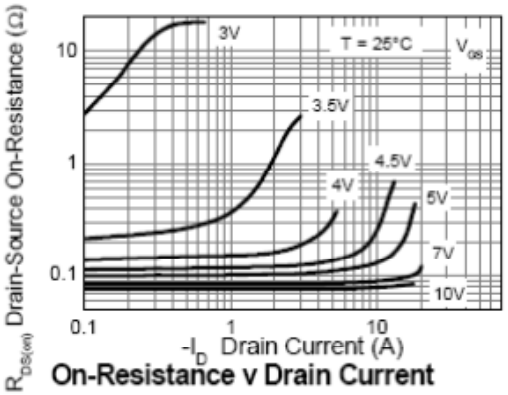
Output Characteristics



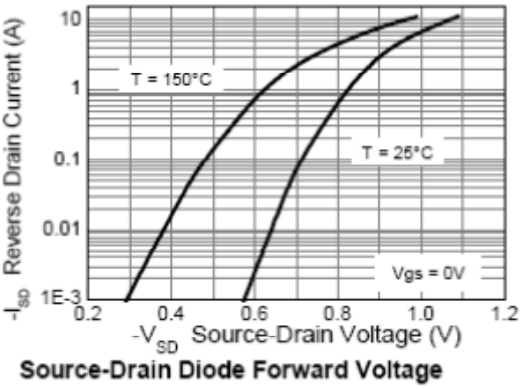
Typical Transfer Characteristics



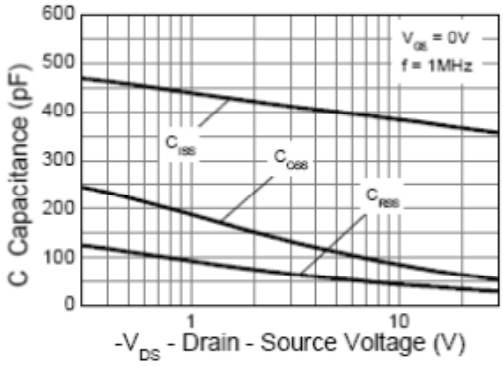
Normalised Curves v Temperature



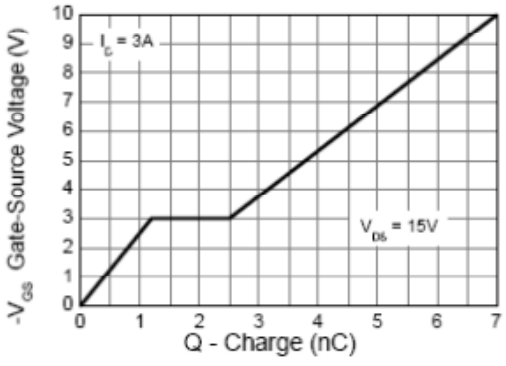
On-Resistance v Drain Current



Source-Drain Diode Forward Voltage

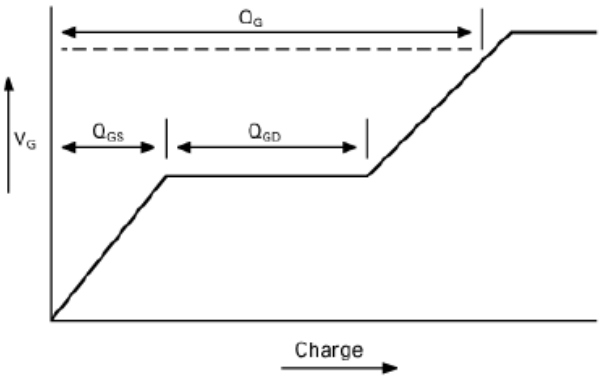


Capacitance v Drain-Source Voltage

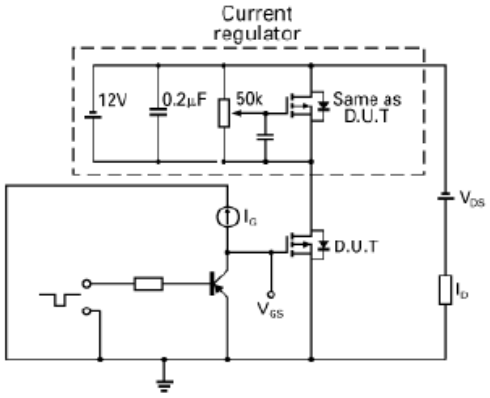


Gate-Source Voltage v Gate Charge

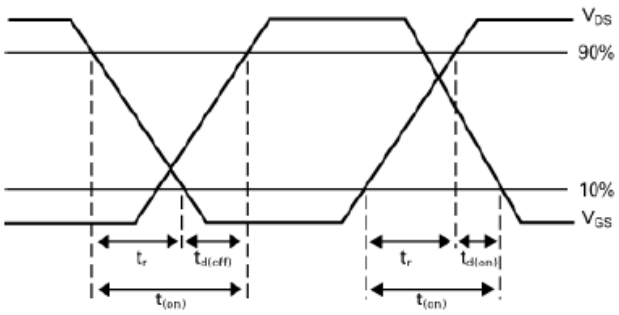
Test Circuits



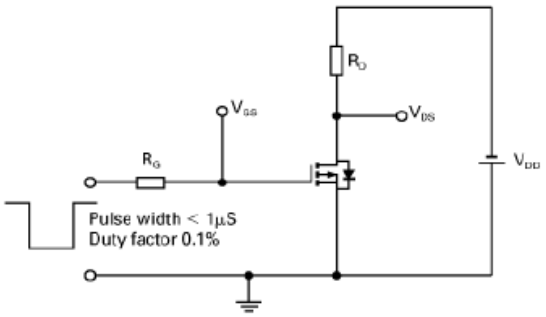
Basic gate charge waveform



Gate charge test circuit



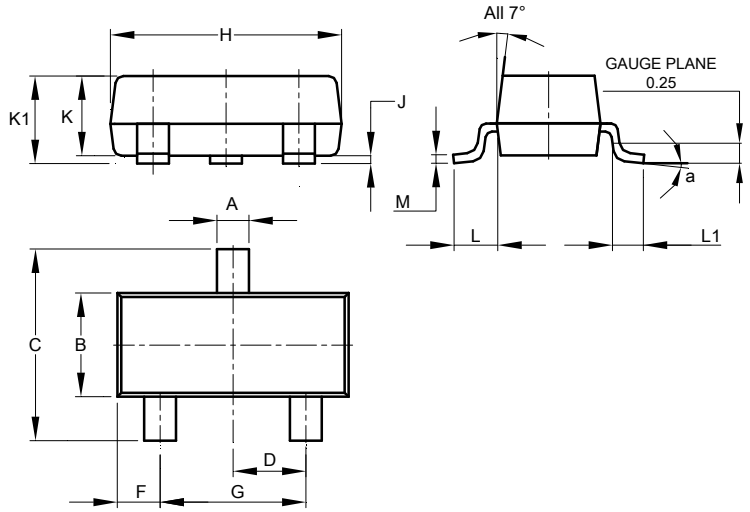
Switching time waveforms



Switching time test circuit

Package Outline Dimensions

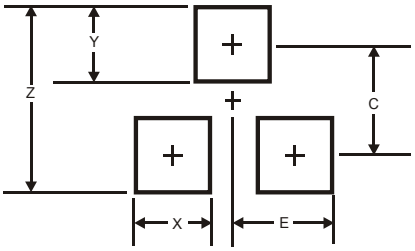
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
α	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

www.diodes.com